Schmitt-Trigger Inverter / CMOS Logic Level Shifter

LSTTL-Compatible Inputs

The MC74VHC1GT14 is a single gate CMOS Schmitt-trigger inverter fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The device input is compatible with TTL-type input thresholds and the output has a full 5 V CMOS level output swing. The input protection circuitry on this device allows overvoltage tolerance on the input, allowing the device to be used as a logic-level translator from 3 V CMOS logic to 5 V CMOS Logic or from 1.8 V CMOS logic to 3 V CMOS Logic while operating at the high-voltage power supply.

The MC74VHC1GT14 input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage. This allows the MC74VHC1GT14 to be used to interface 5 V circuits to 3 V circuits. The output structures also provide protection when $V_{CC}\!=\!0$ V. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc. The MC74VHC1GT14 can be used to enhance noise immunity or to square up slowly changing waveforms.

Features

- High Speed: $t_{PD} = 4.5 \text{ ns (Typ)}$ at $V_{CC} = 5 \text{ V}$
- Low Power Dissipation: $I_{CC} = 1 \mu A \text{ (Max)}$ at $T_A = 25 \text{°C}$
- TTL-Compatible Inputs: $V_{IL} = 0.8 \text{ V}$; $V_{IH} = 2 \text{ V}$
- \bullet CMOS–Compatible Outputs: $V_{OH} > 0.8~V_{CC};~V_{OL} < 0.1~V_{CC}$ @Load
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: FETs = 100; Equivalent Gates = 25
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

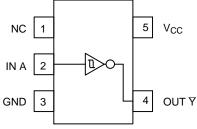


Figure 1. Pinout (Top View)

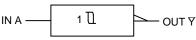


Figure 2. Logic Symbol



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MARKING DIAGRAMS



SC-88A / SC70-5 / SOT-353 DF SUFFIX CASE 419A





TSOP-5 / SOT23-5 / SC59-5 DT SUFFIX CASE 483



VC = Device Code M = Date Code* ■ = Pb-Free Package

■ = Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or position may vary
depending upon manufacturing location.

PIN ASSIGNMENT

1	NC
2	IN A
3	GND
4	OUT ₹
5	V _{CC}

FUNCTION TABLE

A Input	▼ Output
L	Н
Н	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

Symbol	Cł	naracteristics	Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
V _{IN}	DC Input Voltage		-0.5 to +7.0	V
V _{OUT}	DC Output Voltage	$V_{CC} = 0$ High or Low State	-0.5 to 7.0 -0.5 to V _{CC} + 0.5	V
I _{IK}	Input Diode Current		-20	mA
I _{OK}	Output Diode Current	$V_{OUT} < GND; V_{OUT} > V_{CC}$	+20	mA
lout	DC Output Current, per Pin		+25	mA
I _{CC}	DC Supply Current, V _{CC} and GND		+50	mA
P _D	Power Dissipation in Still Air	SC-88A, TSOP-5	200	mW
$\theta_{\sf JA}$	Thermal Resistance	SC-88A, TSOP-5	333	°C/W
TL	Lead Temperature, 1 mm from Case for	r 10 secs	260	°C
TJ	Junction Temperature Under Bias		+150	°C
T _{stg}	Storage Temperature		-65 to +150	°C
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	> 2000 > 200 N/A	V
I _{Latchup}	Latchup Performance	Above V _{CC} and Below GND at 125°C (Note 4)	±500	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Tested to EIA/JESD22-A114-A
- 2. Tested to EIA/JESD22-A115-A
- 3. Tested to JESD22-C101-A
- 4. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V _{CC}	DC Supply Voltage	3.0	5.5	V
V_{IN}	DC Input Voltage	0.0	5.5	V
V _{OUT}	DC Output Voltage $V_{CC} = 0$ High or Low State	0.0 0.0	5.5 V _{CC}	V
T _A	Operating Temperature Range	-55	+125	°C
t _r , t _f	Input Rise and Fall Time $ V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V} $	-	No Limit No Limit	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

Device Junction Temperature versus Time to 0.1% Bond Failures

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

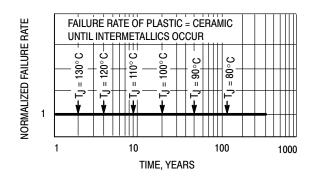


Figure 3. Failure Rate vs. Time Junction Temperature

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	Т	A = 25°	С	T _A ≤	85°C	-55 ≤ T _A	≤ 125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{T+}	Positive Threshold Voltage		3.0 4.5 5.5	1.20 1.58 1.79	1.40 1.74 1.94	1.60 2.00 2.10		1.6 2.0 2.1		1.6 2.0 2.1	V
V _T	Negative Threshold Voltage		3.0 4.5 5.5	0.35 0.5 0.6	0.76 1.01 1.13	0.93 1.18 1.29	0.35 0.5 0.6		0.35 0.5 0.6		V
V _H	Hysteresis Voltage		3.0 4.5 5.5	0.30 0.40 0.50	0.64 0.73 0.81	1.20 1.40 1.60	0.30 0.40 0.50	1.20 1.40 1.60	0.30 0.40 0.50	1.20 1.40 1.60	V
V _{OH}	Minimum High–Level Output Voltage	$V_{IN} \le V_T - Min$ $I_{OH} = -50 \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		I _{OH} = -4 mA I _{OH} = -8 mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
V _{OL}	Maximum Low–Level Output Voltage	$V_{IN} \ge V_T + Max$ $I_{OL} = 50 \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		I _{OL} = 4 mA I _{OL} = 8 mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μΑ
Icc	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			1.0		20		40	μΑ
Ісст	Quiescent Supply Current	Input: V _{IN} = 3.4 V	5.5			1.35		1.50		1.65	mA
I _{OPD}	Output Leakage Current	V _{OUT} = 5.5 V	0.0			0.5		5.0		10	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS $C_{load} = 50$ pF, Input $t_r/t_f = 3.0$ ns

				T	_A = 25°(2	T _A ≤	85°C	-55 ≤ T _A	≤ 125°C	
Symbol	Parameter	Test Condition	ons	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A to ₹	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		7.0 8.4	12.8 16.3	1.0 1.0	15.0 18.5	1.0 1.0	17.0 20.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		4.5 5.8	8.6 10.6	1.0 1.0	10.0 12.0	1.0 1.0	11.5 13.5	
C _{IN}	Maximum Input Capacitance				5	10		10		10	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Note 5)	10	pF

^{5.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

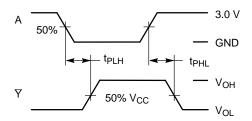
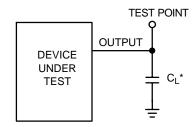


Figure 4. Switching Waveforms



^{*}Includes all probe and jig capacitance

Figure 5. Test Circuit

ORDERING INFORMATION

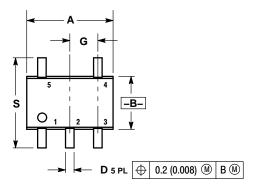
Device	Package	Shipping [†]
M74VHC1GT14DFT1G	SC70-5/SC-88A/SOT-353 (Pb-Free)	3000/Tape & Reel
NLVVHC1GT14DFT1G*	SC70-5/SC-88A/SOT-353 (Pb-Free)	3000/Tape & Reel
M74VHC1GT14DFT2G	SC70-5/SC-88A/SOT-353 (Pb-Free)	3000/Tape & Reel
NLVVHC1GT14DFT2G*	SC70-5/SC-88A/SOT-353 (Pb-Free)	3000/Tape & Reel
M74VHC1GT14DTT1G	SOT23-5/TSOP-5/SC59-5 (Pb-Free)	3000/Tape & Reel

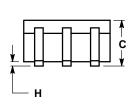
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging

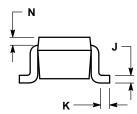
Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable.

PACKAGE DIMENSIONS

SC-88A (SC-70-5/SOT-353) CASE 419A-02 ISSUE L



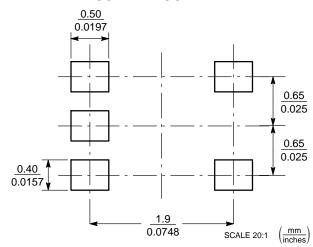




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 419A-01 OBSOLETE. NEW STANDARD 419A-02.
 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

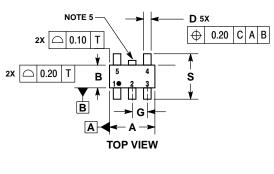
	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
С	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026	BSC	0.65	BSC
Н		0.004		0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20	REF
S	0.079	0.087	2.00	2.20

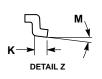
SOLDER FOOTPRINT

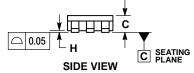


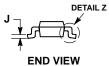
PACKAGE DIMENSIONS

TSOP-5 **CASE 483 ISSUE M**







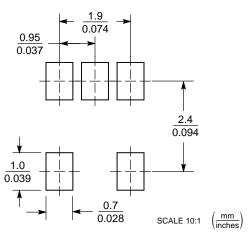


NOTES

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL. DIMENSIONS A AND B DO NOT INCLUDE MOLD
- FLASH, PROTRUSIONS, OR GATE BURRS. MOLD
 FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT
 EXCEED 0.15 PER SIDE. DIMENSION A.
 OPTIONAL CONSTRUCTION: AN ADDITIONAL
 TRIMMED LEAD IS ALLOWED IN THIS LOCATION.
- TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2

	MILLIMETERS					
DIM	MIN	MAX				
Α	2.85	3.15				
В	1.35	1.65				
С	0.90	1.10				
D	0.25	0.50				
G	0.95	BSC				
Н	0.01	0.10				
J	0.10	0.26				
K	0.20	0.60				
М	0 °	10 °				
S	2.50	3.00				

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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